Electronic Supplementary Information (ESI)

An in-situ study of nucleation and growth of aqueous phase deposited Ga:ZnO transparent conducting films using optical techniques

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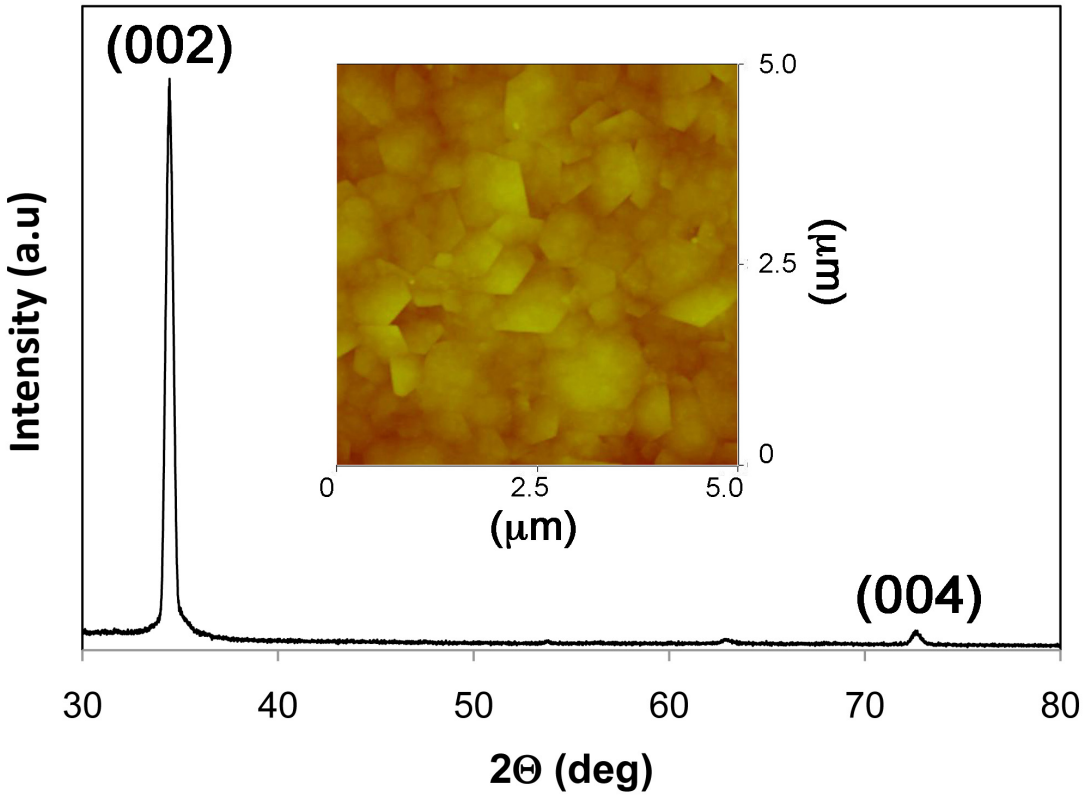

Fig. S1 XRD of Ga:ZnO film grown with 1.92mM $Ga(NO_3)_3$ and 1.86mM trisodium citrate. Inset: AFM scan across a 5x5μm region. Films had a RMS roughness of 12nm.

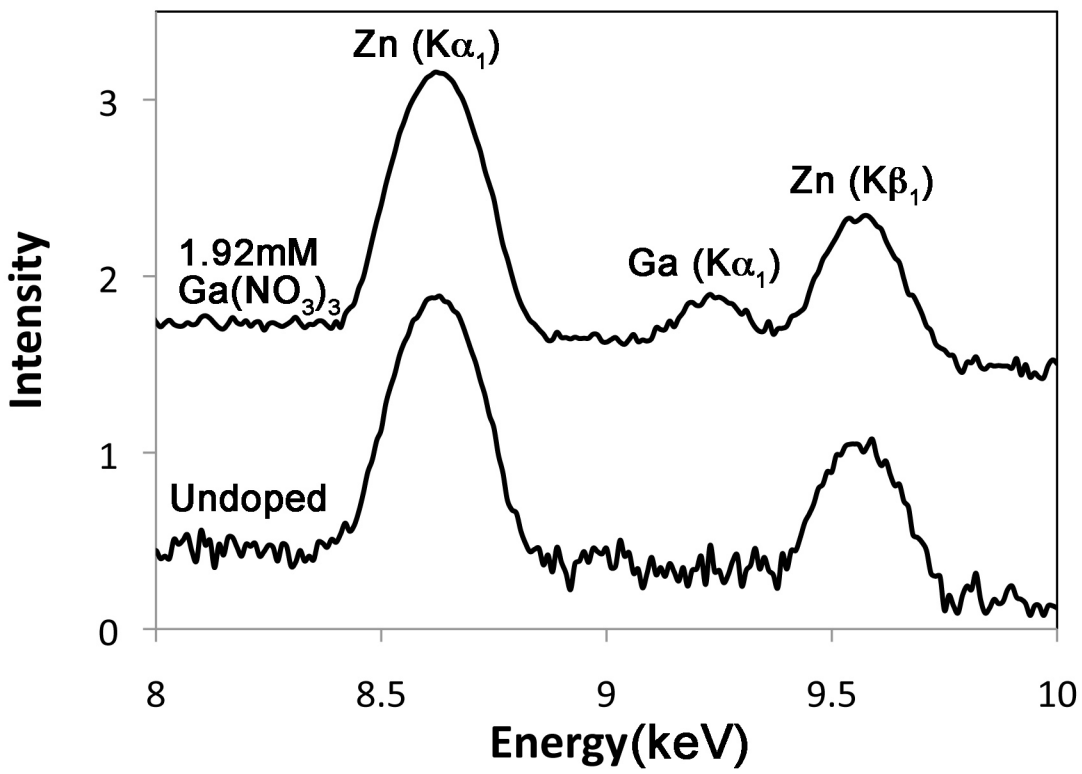

Fig. S2 – EDX spectra of undoped films and films doped with 1.92mM of $Ga(NO_3)_3$. Doped samples had an additional Ga (Kα1) peak centered at 9.251keV.

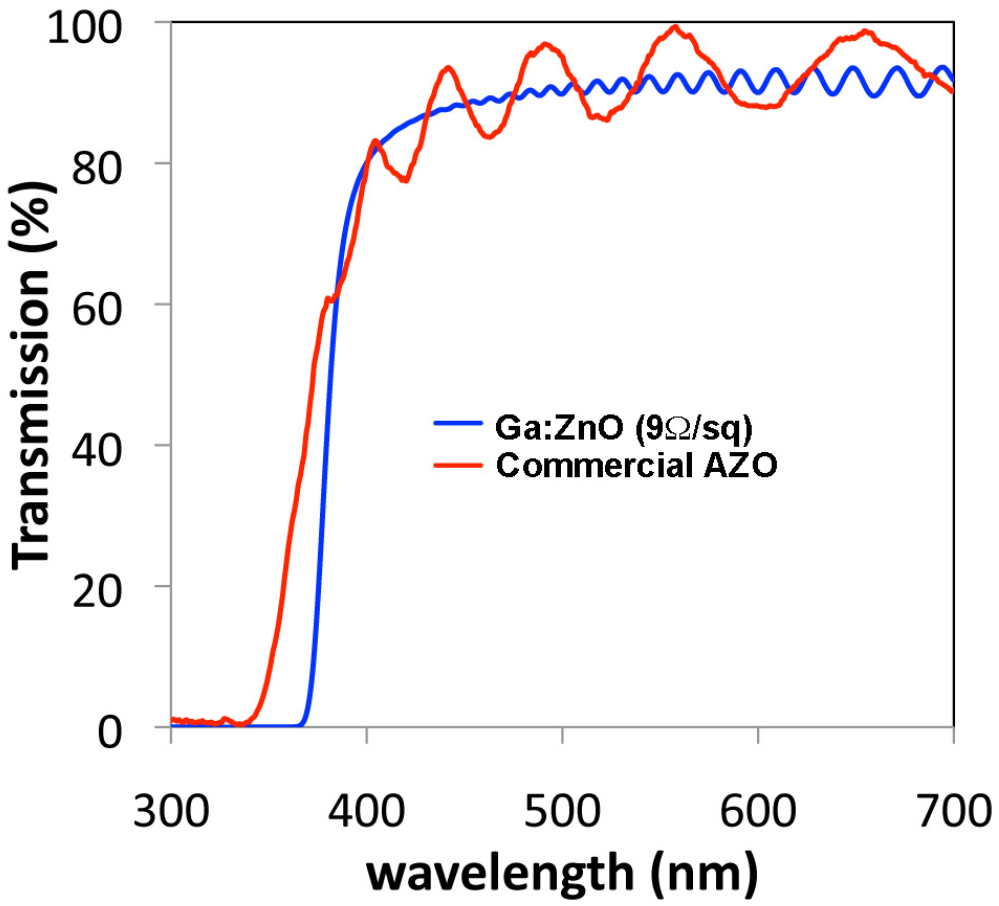

Fig. S3- Transmission spectra of commercial AZO substrate and a 9Ω/sq Ga:ZnO substrate